



STD16NF25 STF16NF25 - STP16NF25

N-channel 250V - 0.195Ω - 13A - DPAK/TO-220/TO-220FP
Low gate charge STripFET™ II Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} Max	I _D	P _w
STD16NF25	250V	<0.235Ω	13A	90W
STF16NF25	250V	<0.235Ω	13A ⁽¹⁾	25W
STP16NF25	250V	<0.235Ω	13A	90W

1. Limited only by maximum temperature allowed

- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Application

- Switching applications

Description

This Power MOSFET series realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

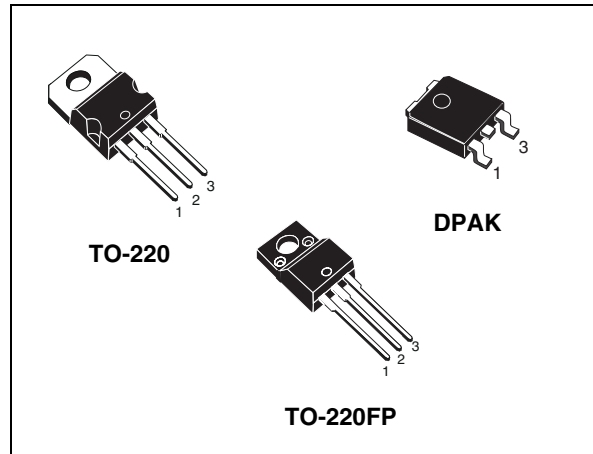


Figure 1. Internal schematic diagram

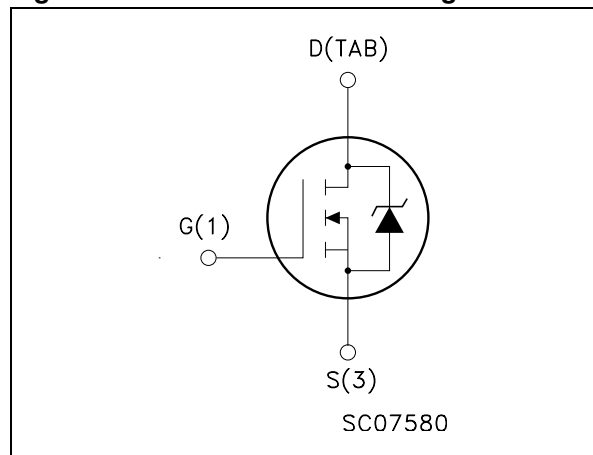


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD16NF25	16NF25	DPAK	Tape & reel
STF16NF25	16NF25	TO-220FP	Tube
STP16NF25	16NF25	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		DPAK TO-220	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	250		V
V_{GS}	Gate- source voltage	± 20		V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	13	$13^{(1)}$	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	8.19	$8.19^{(1)}$	A
$I_{DM}^{(2)}$	Drain current (pulsed)	52	$52^{(1)}$	A
P_{tot}	Total dissipation at $T_C = 25^\circ\text{C}$	90	25	W
	Derating Factor	0.72	0.2	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{s}; T_C=25^\circ\text{C}$)	--	2500	V
T_{stg}	Storage temperature	-55 to 150		$^\circ\text{C}$
T_j	Max. operating junction temperature			

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 13\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} \leq 80\% V_{(BR)DSS}$, $T_j \leq T_{JMAX}$

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		TO-220	DPAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	1.39		5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction to pcb max	--	50	--	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	100	62.5	$^\circ\text{C}/\text{W}$
T_J	Maximum lead temperature for soldering purpose	300			$^\circ\text{C}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j Max)	13	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25^\circ\text{C}$, $I_d=13\text{A}$, $V_{dd}=50\text{V}$)	100	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{mA}$, $V_{GS} = 0$	250			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max ratings}$ $V_{DS} = \text{max ratings}$, $T_C = 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$, $I_D = 6.5\text{A}$		0.195	0.235	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{V}$, $I_D = 6.5\text{A}$		10		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}$, $f = 1\text{MHz}$, $V_{GS} = 0$		680 125 20		pF pF pF
$C_{oss\text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{DS} = 0\text{V to } 200\text{V}$, $V_{GS} = 0$		48		pF
R_G	Intrinsic gate resistance	$f=1\text{MHz}$, open drain		2.1		Ω
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 125\text{V}$, $I_D = 6.5\text{A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{V}$ (see Figure 18)		9 17 35 17		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 200\text{V}$, $I_D = 6.5\text{A}$, $V_{GS} = 10\text{V}$ (see Figure 19)		18 3 8		nC nC nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%.

2. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80%

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				13 52	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 13A$, $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 13A$, $di/dt = 100A/\mu s$, $V_{DD} = 60V$ (see Figure 20)		133 651 10		ns μC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 13A$, $di/dt = 100A/\mu s$, $V_{DD} = 60V$, $T_j = 150^\circ C$ (see Figure 20)		157 895 11		ns μC A

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

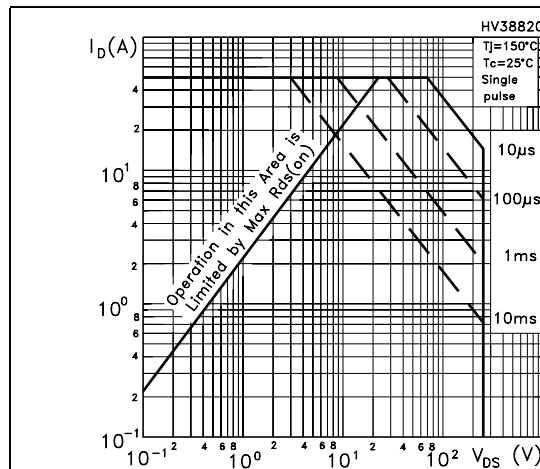


Figure 3. Thermal impedance for TO-220

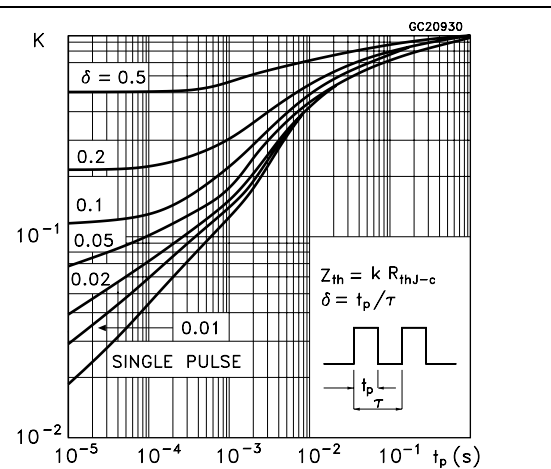


Figure 4. Safe operating area for TO-220FP

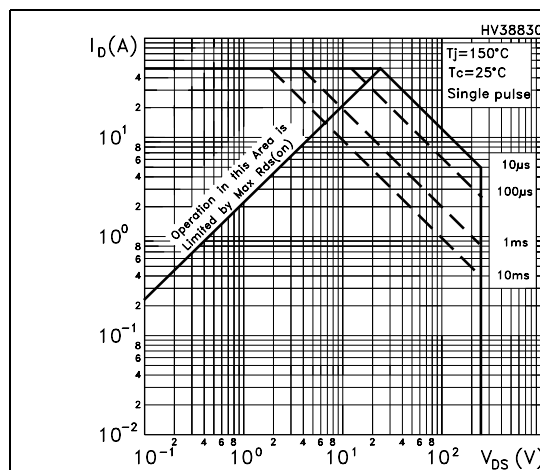


Figure 5. Thermal impedance for TO-220FP

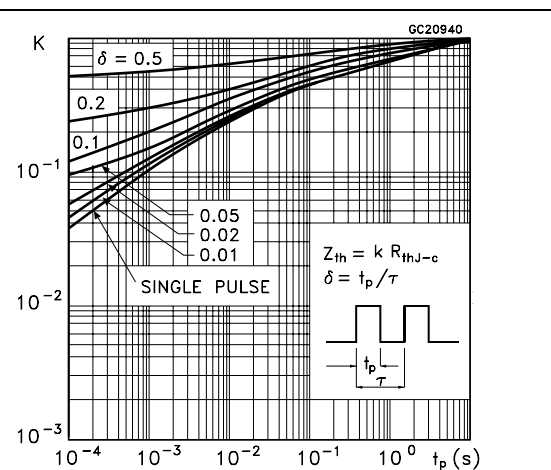


Figure 6. Safe operating area for DPAK

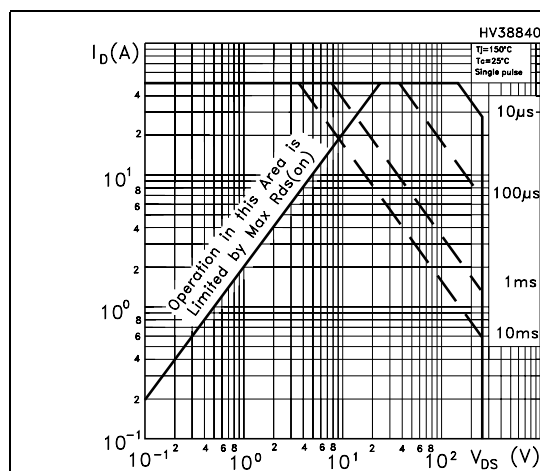


Figure 7. Thermal impedance for DPAK

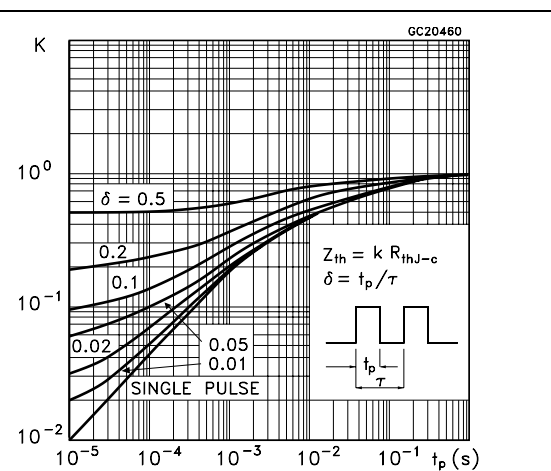


Figure 8. Output characteristics

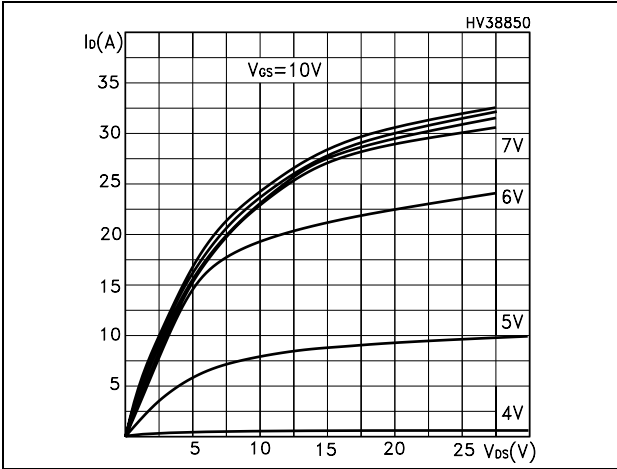


Figure 9. Transfer characteristics

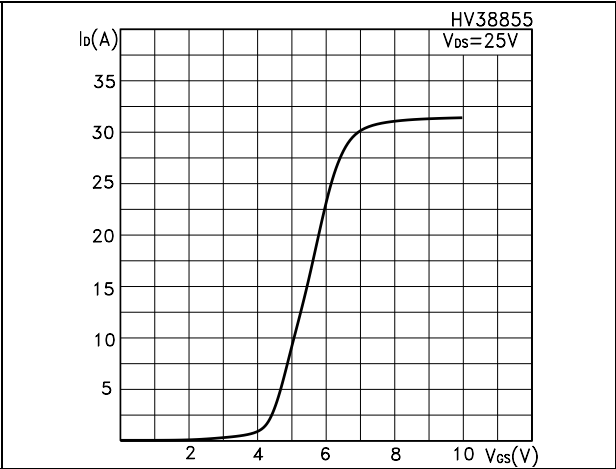


Figure 10. Normalized BV_{DSS} vs temperature

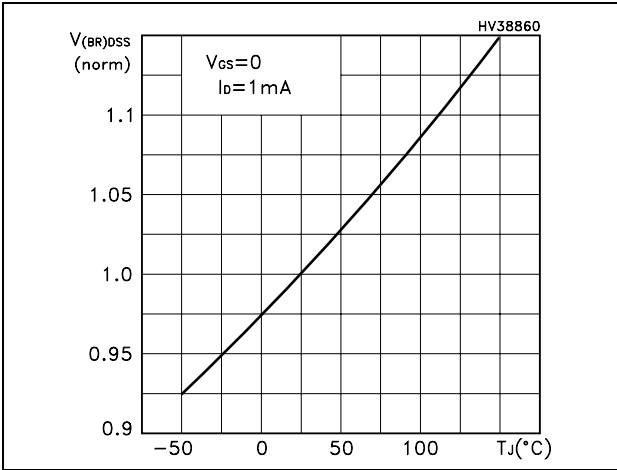


Figure 11. Static-drain source on resistance

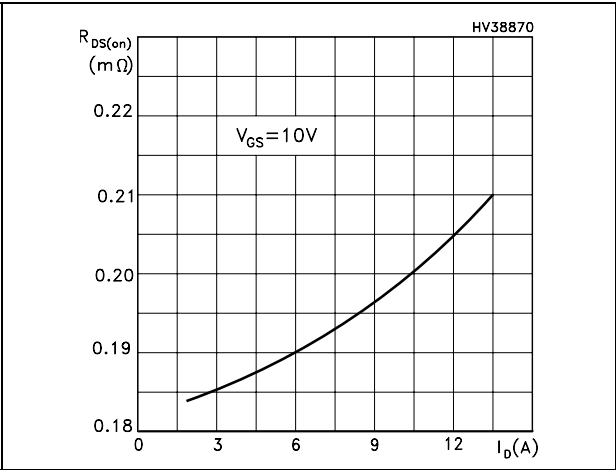


Figure 12. Gate charge vs gate-source voltage

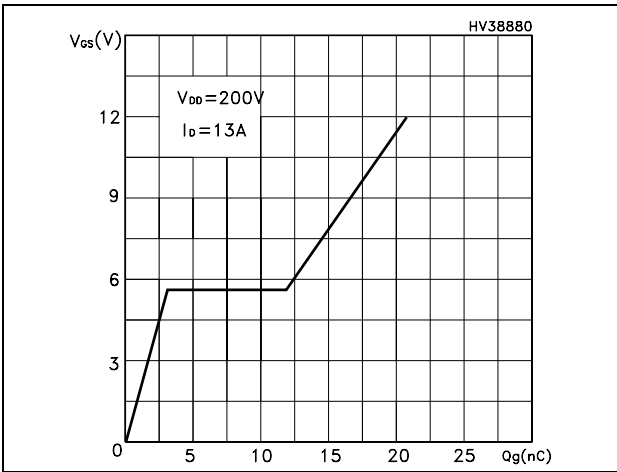


Figure 13. Capacitance variations

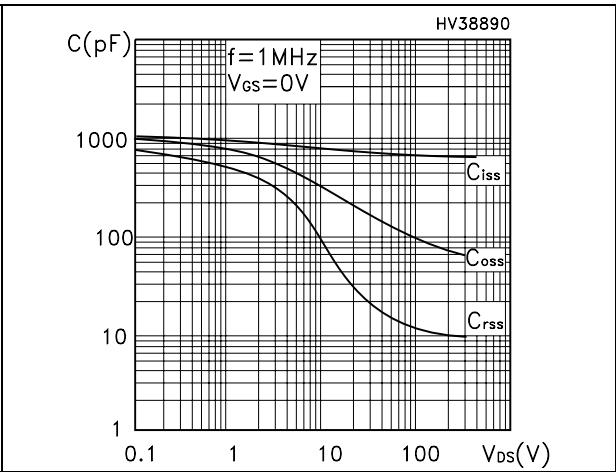


Figure 14. Normalized gate threshold voltage vs temperature

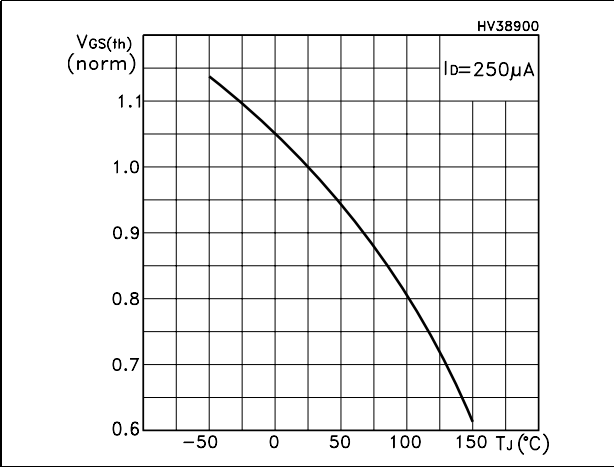


Figure 15. Normalized on resistance vs temperature

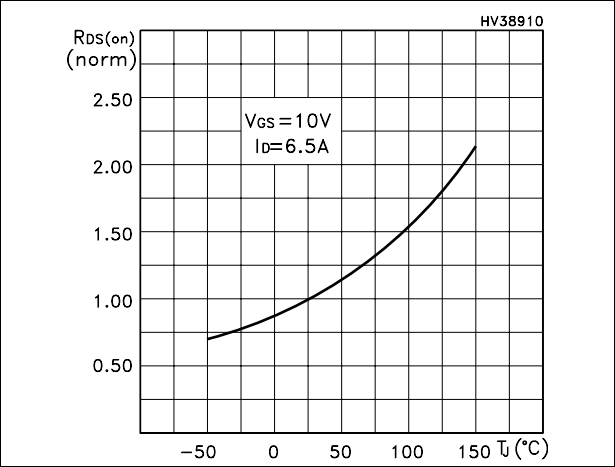


Figure 16. Source-drain diode forward characteristics

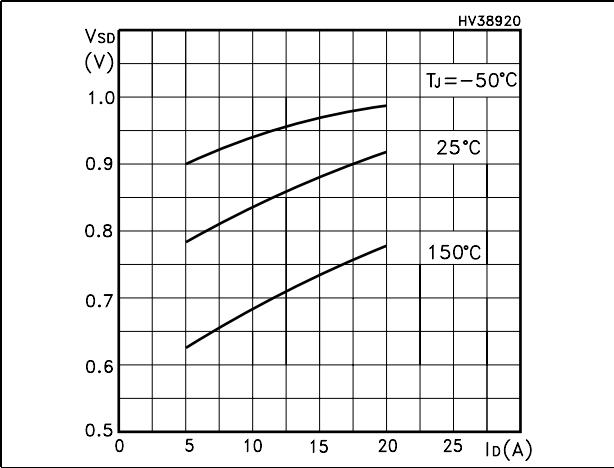
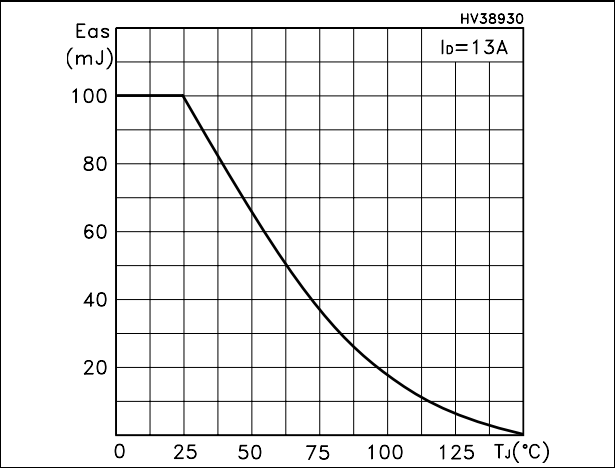


Figure 17. Maximum avalanche energy vs starting TJ



3 Test circuit

Figure 18. Switching times test circuit for resistive load

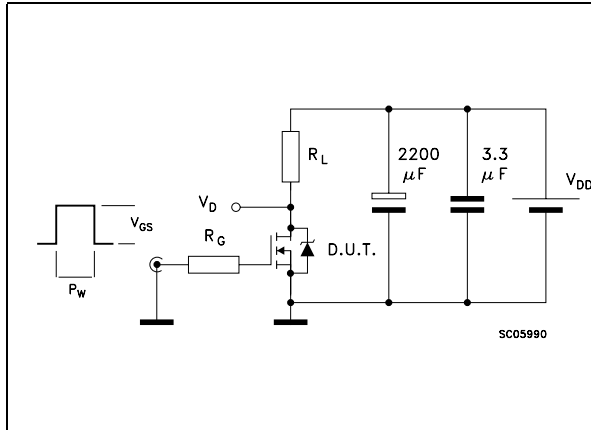


Figure 19. Gate charge test circuit

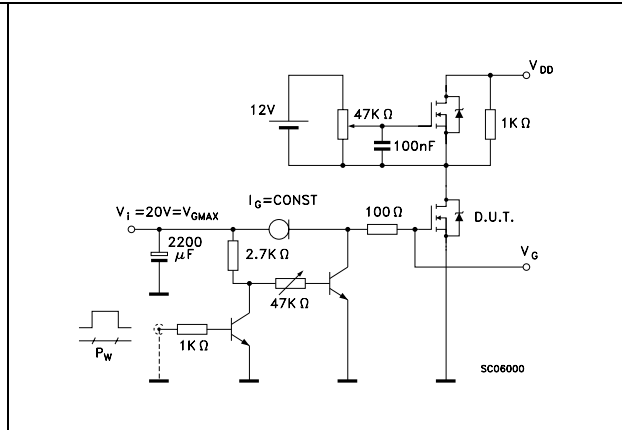


Figure 20. Test circuit for inductive load switching and diode recovery times

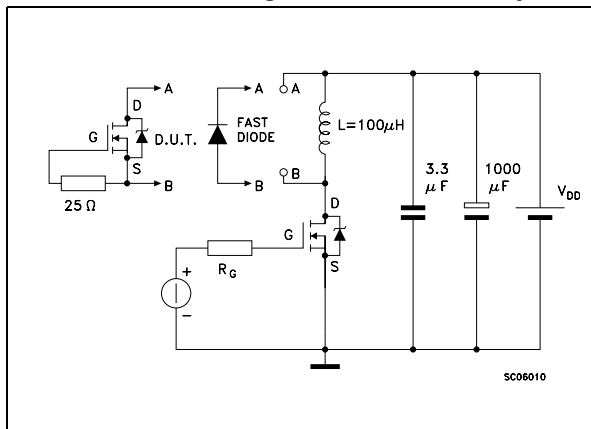


Figure 21. Unclamped Inductive load test circuit

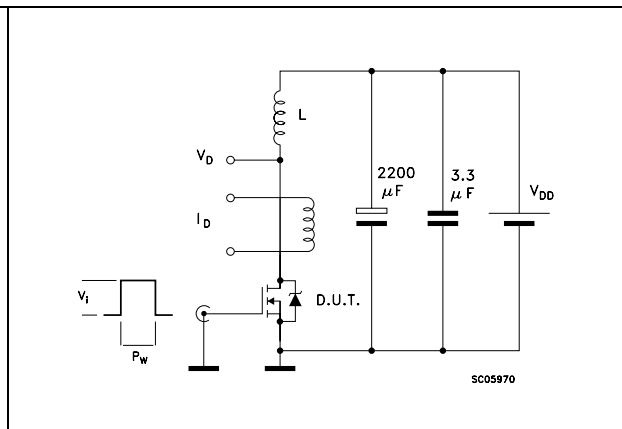


Figure 22. Unclamped inductive waveform

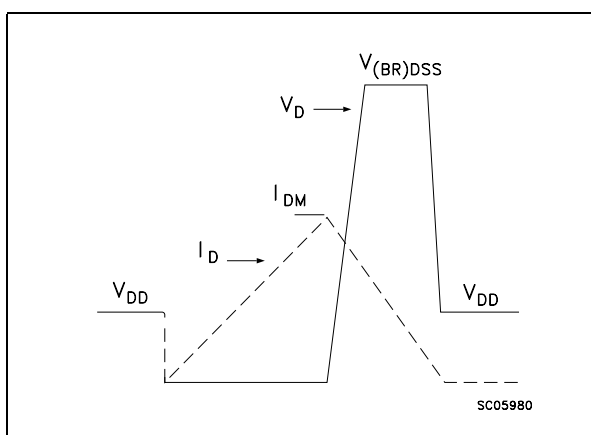
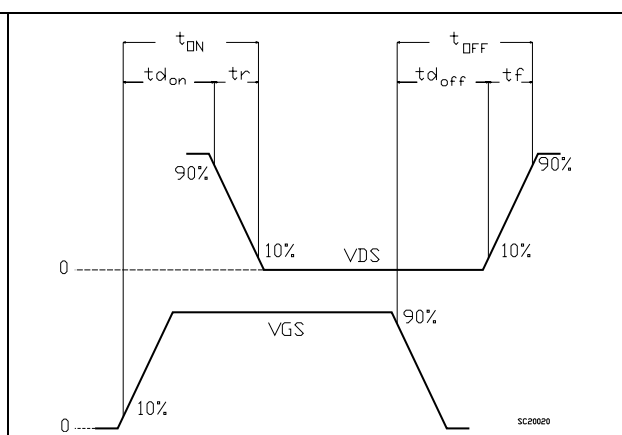


Figure 23. Switching time waveform

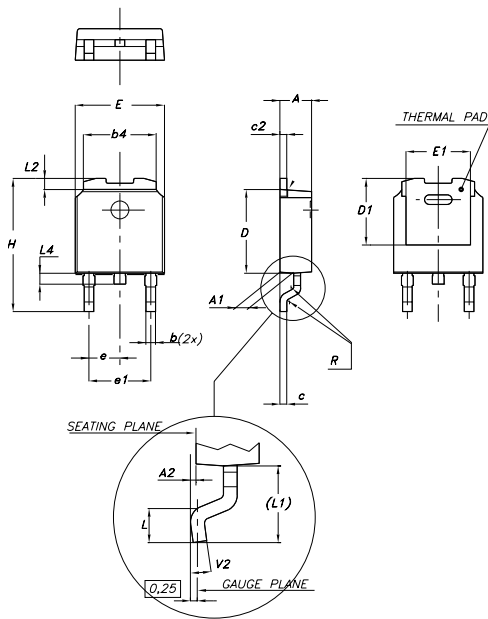


4 **Package mechanical data**

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

DPAK MECHANICAL DATA

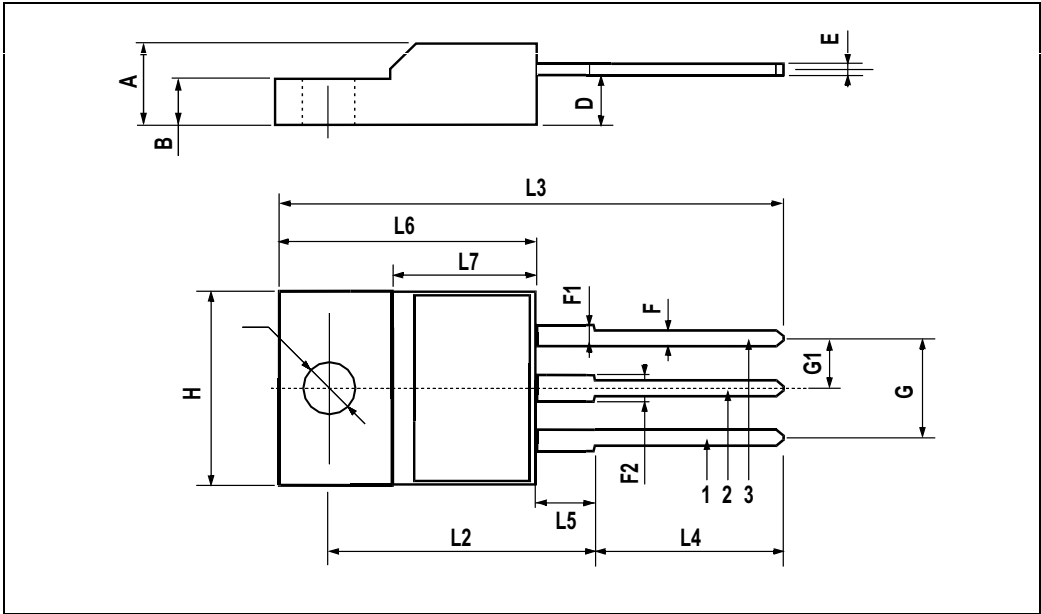
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



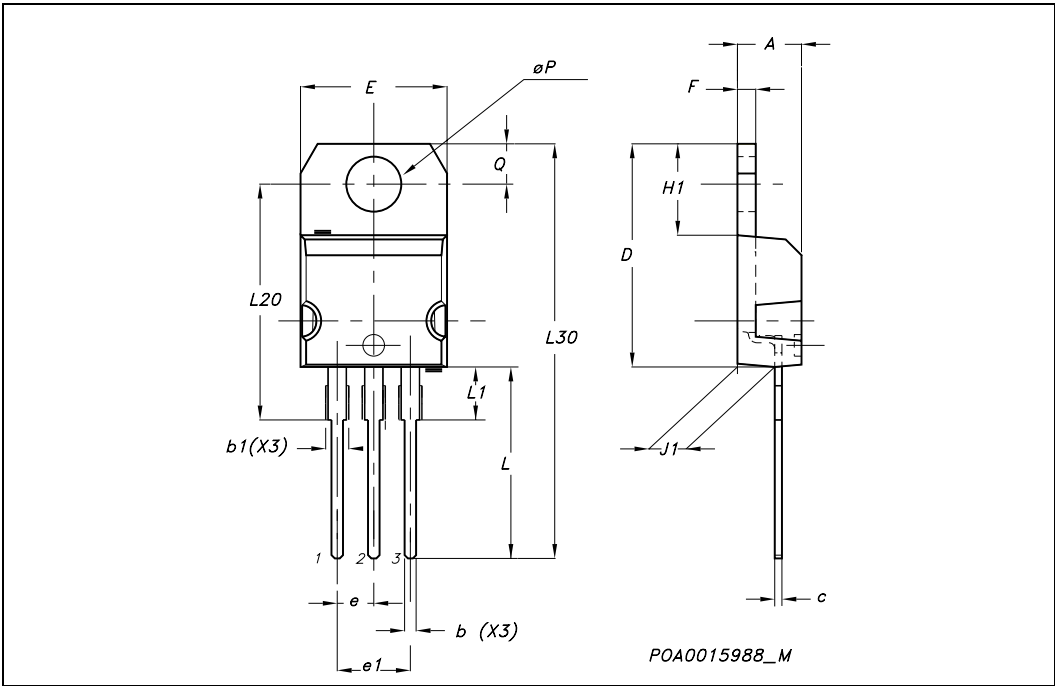
0068772-F

TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126

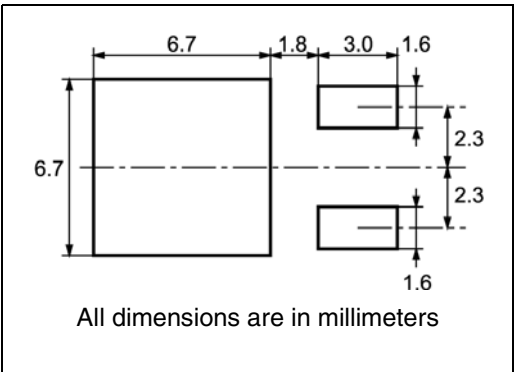


TO-220 MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

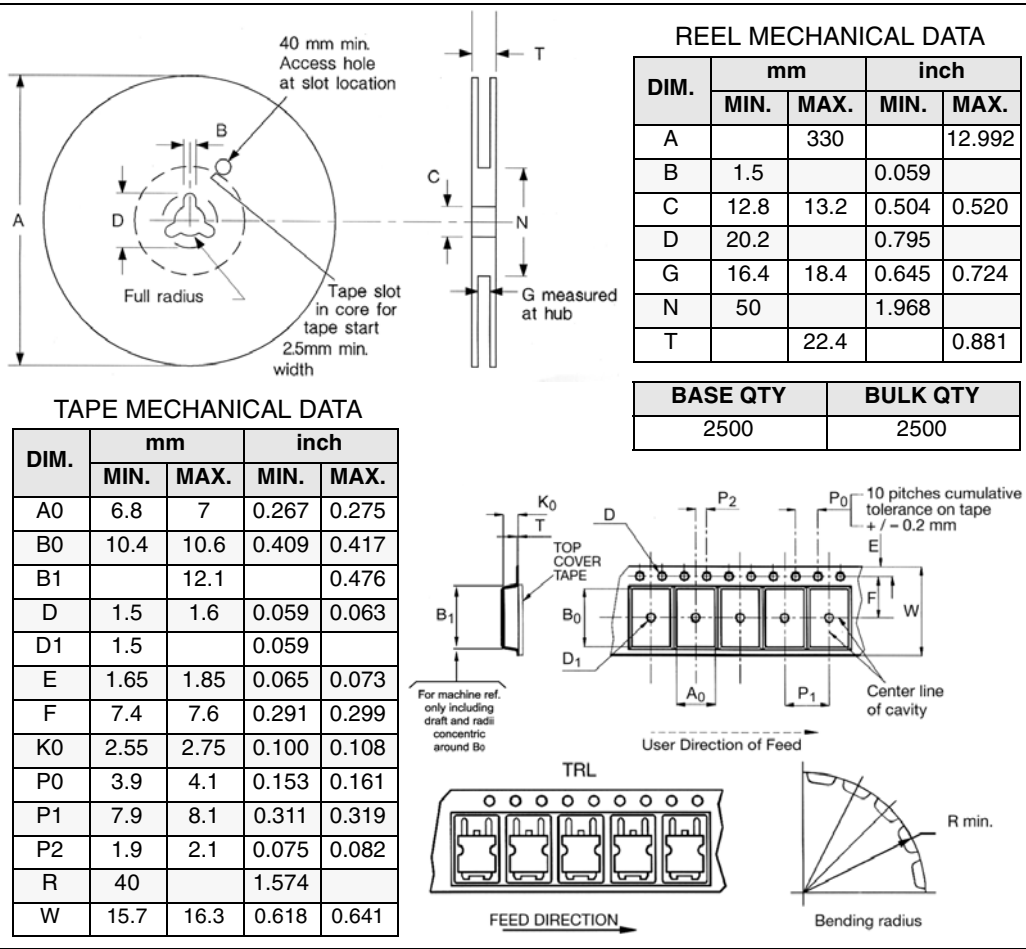


5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 8. Document revision history

Date	Revision	Changes
12-Oct-2007	1	Initial release
16-Oct-2007	2	Modified: Figure 13: Capacitance variations

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